Automotive Dual P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V_{DS} (V)	- 60
$R_{DS(on)}$ (Ω) at V_{GS} = - 10 V	0.085
$R_{DS(on)}$ (Ω) at V_{GS} = - 4.5 V	0.115
I_D (A) per leg	- 4.4
Configuration	Dual

FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified
- 100 % R_g and UIS Tested
- Material categorization:
  For definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

Pb Pb-free

RoHS COMPLIANT

HALOGEN FREE

SO-8

Top View

P-Channel MOSFET   P-Channel MOSFET
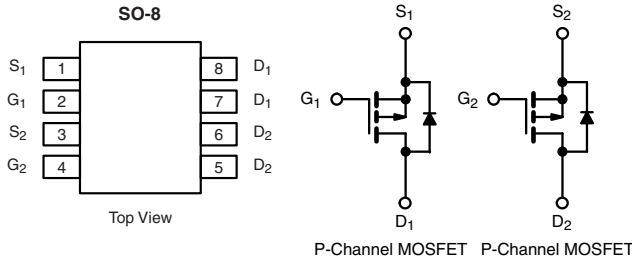
ORDERING INFORMATION

Package	SO-8
Lead (Pb)-free and Halogen-free	SQ4961EY-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C	I_D	- 4.4	A
	T_C = 125 °C		- 2.5	
Continuous Source Current (Diode Conduction)		I_S	- 3	
Pulsed Drain Current[a]		I_{DM}	- 18	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	- 20	
Single Pulse Avalanche Energy		E_{AS}	20	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	3.3	W
	T_C = 125 °C		1.1	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount[b]	R_{thJA}	105	°C/W
Junction-to-Foot (Drain)		R_{thJF}	45	

Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)

| PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA		- 60	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA		- 1.5	- 2.0	- 2.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = - 60 V	-	-	- 1	µA
		V_{GS} = 0 V	V_{DS} = - 60 V, T_J = 125 °C	-	-	- 50	
		V_{GS} = 0 V	V_{DS} = - 60 V, T_J = 175 °C	-	-	- 150	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = - 10 V	V_{DS} ≤ - 5 V	- 12	-	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V	I_D = - 3.5 A	-	0.070	0.085	Ω
		V_{GS} = - 10 V	I_D = - 3.5 A, T_J = 125 °C	-	-	0.142	
		V_{GS} = - 10 V	I_D = - 3.5 A, T_J = 175 °C	-	-	0.176	
		V_{GS} = - 4.5 V	I_D = - 2.5 A	-	0.095	0.115	
Forward Transconductance[b]	g_{fs}	V_{DS} = - 15 V, I_D = - 3.5 A		-	9	-	S
Dynamic[b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = - 30 V, f = 1 MHz	-	912	1140	pF
Output Capacitance	C_{oss}			-	100	125	
Reverse Transfer Capacitance	C_{rss}			-	60	75	
Total Gate Charge[c]	Q_g	V_{GS} = - 10 V	V_{DS} = - 30 V, I_D = - 4.3 A	-	26.5	40	nC
Gate-Source Charge[c]	Q_{gs}			-	3.8	-	
Gate-Drain Charge[c]	Q_{gd}			-	5.8	-	
Gate Resistance	R_g	f = 1 MHz		3	-	16	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 30 V, R_L = 8.8 Ω I_D ≅ - 3.4 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	11	17	ns
Rise Time[c]	t_r			-	13	20	
Turn-Off Delay Time[c]	$t_{d(off)}$			-	36	54	
Fall Time[c]	t_f			-	8	12	
Source-Drain Diode Ratings and Characteristics[b]							
Pulsed Current[a]	I_{SM}			-	-	- 18	A
Forward Voltage	V_{SD}	I_F = - 3 A, V_{GS} = 0 V		-	- 0.84	- 1.2	V

Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
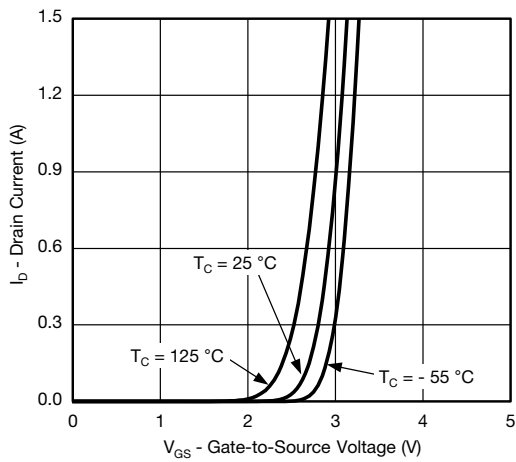
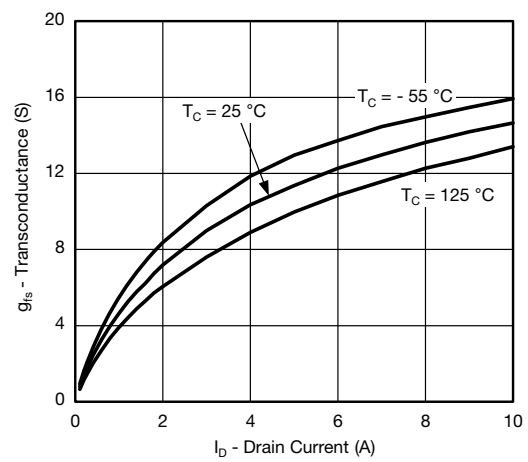## TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)
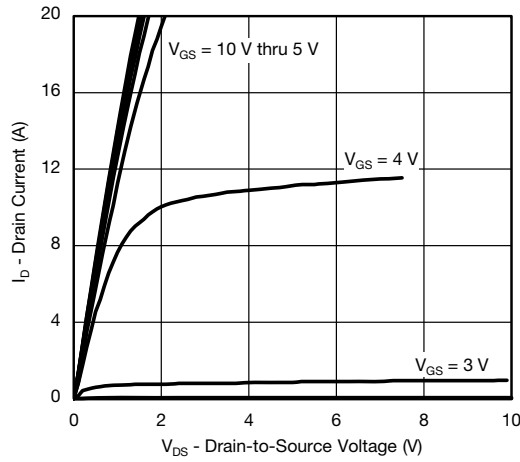
Output Characteristics
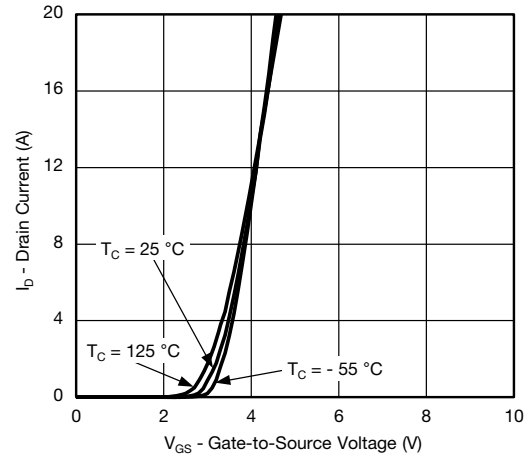
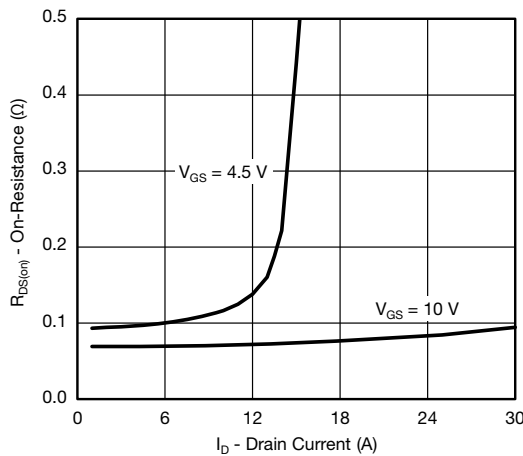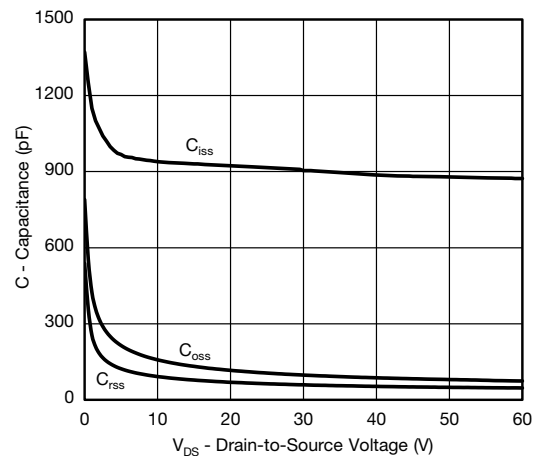**Transfer Characteristics**
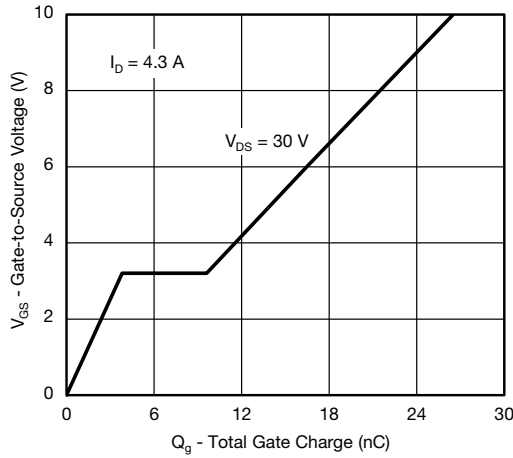

Transfer Characteristics

Transconductance
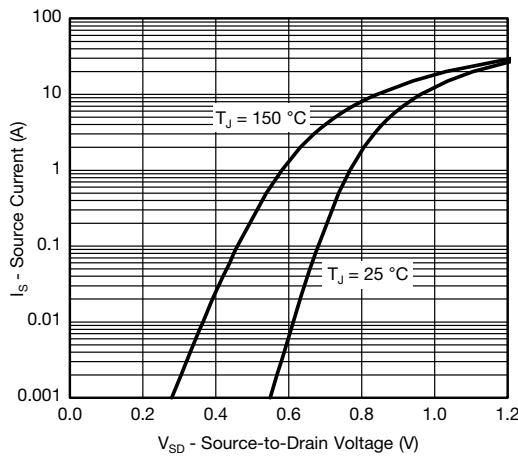

On-Resistance vs. Drain Current

Capacitance

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)
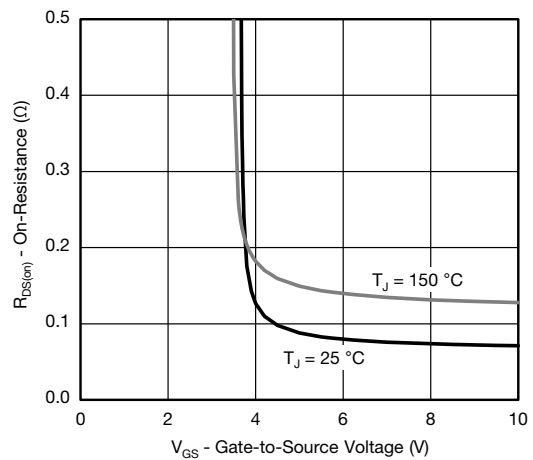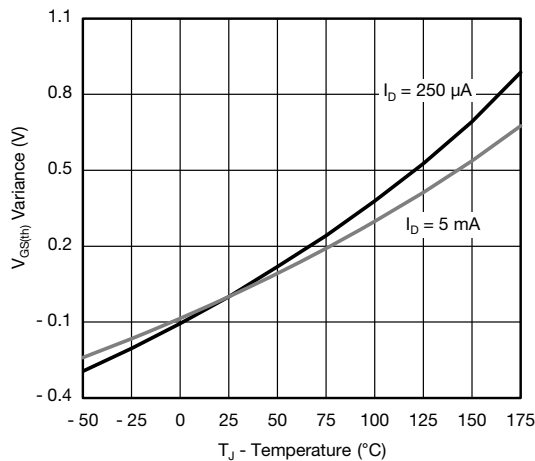

Gate Charge
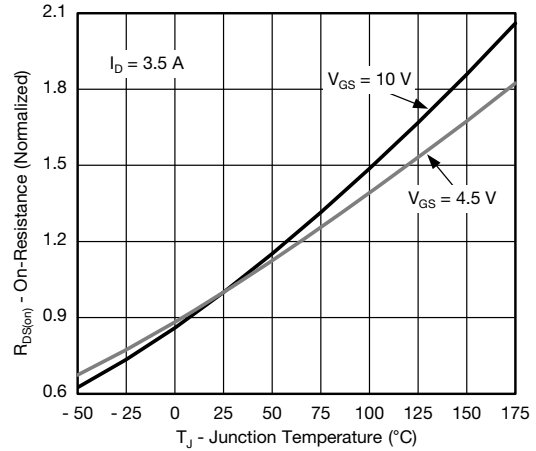
On-Resistance vs. Junction Temperature
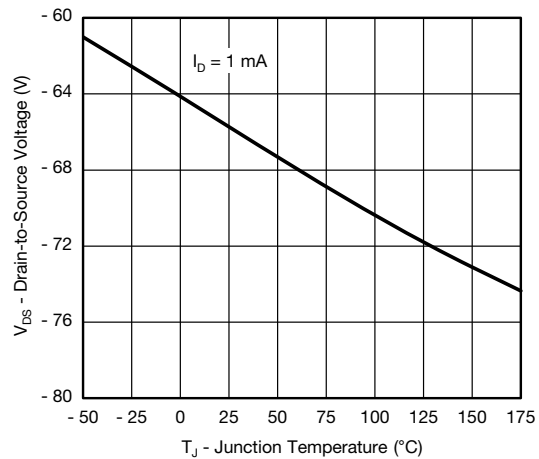

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)
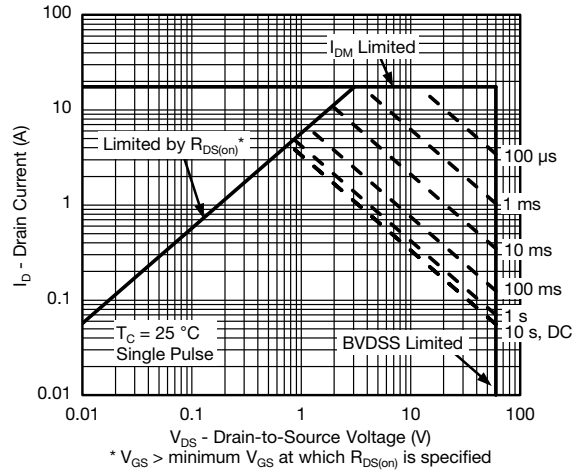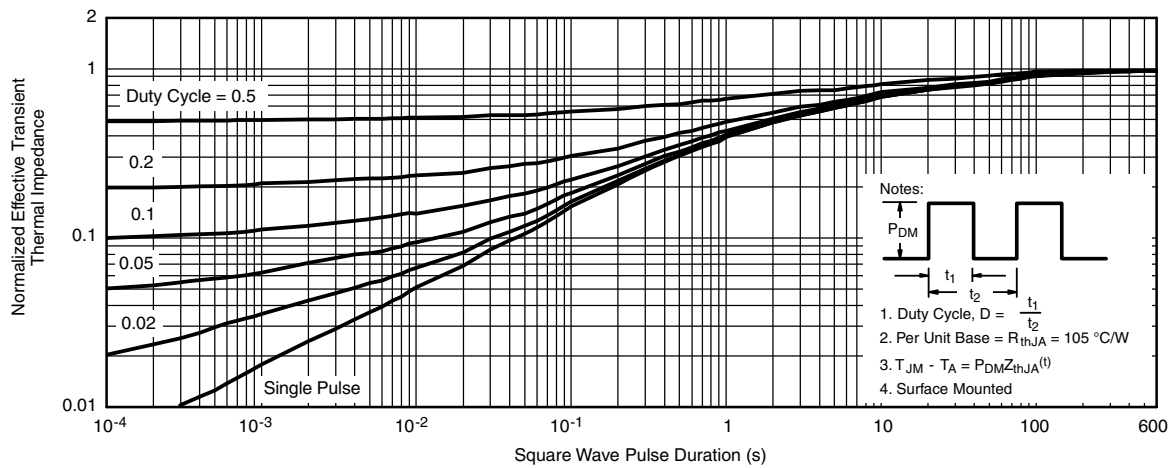
I_{DM} Limited

Limited by $R_{DS(on)}$*

100 µs
1 ms
10 ms
100 ms
1 s
10 s, DC

T_C = 25 °C
Single Pulse

BVDSS Limited

I_D - Drain Current (A)

V_{DS} - Drain-to-Source Voltage (V)
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

Duty Cycle = 0.5
0.2
0.1
0.05
0.02

Single Pulse

Normalized Effective Transient
Thermal Impedance

Square Wave Pulse Duration (s)

Notes:

P_{DM}

t_1
t_2

1. Duty Cycle, D = $\dfrac{t_1}{t_2}$
2. Per Unit Base = R_{thJA} = 105 °C/W
3. T_{JM} - T_A = $P_{DM}Z_{thJA}^{(t)}$
4. Surface Mounted

Normalized Thermal Transient Impedance, Junction-to-Ambient

For technical questions, contact: automostechsupport@vishay.com

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)
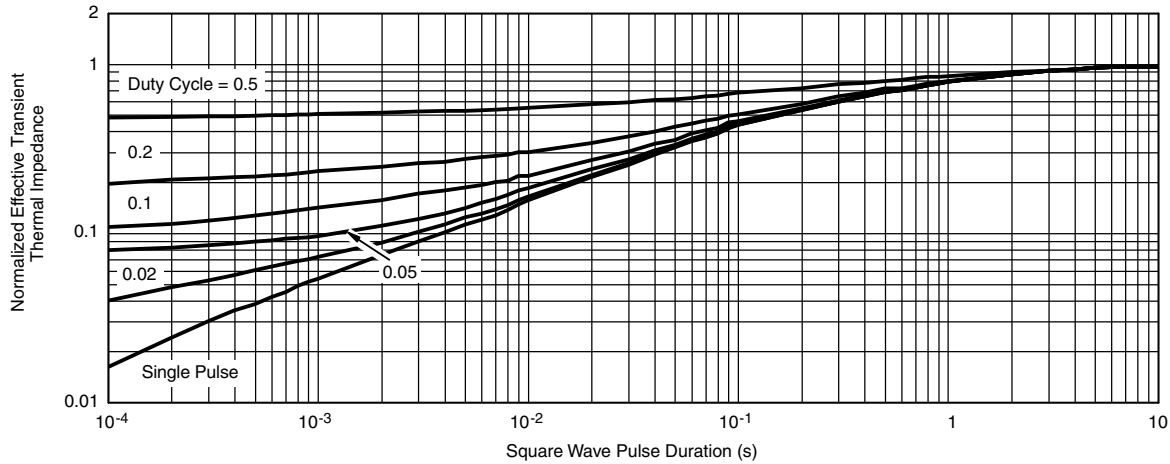
Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

  are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

For technical questions, contact: automostechsupport@vishay.com

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SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012

	MILLIMETERS		INCHES	
DIM	**Min**	**Max**	**Min**	**Max**
A	1.35	1.75	0.053	0.069
A_1	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8

Recommended Minimum Pads
Dimensions in Inches/(mm)

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APPLICATION NOTE

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